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Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

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Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	276480
Number of I/O	223
Number of Gates	1500000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	484-BGA
Supplier Device Package	484-FPBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/afs1500-1fg484i

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Routing Architecture

The routing structure of Fusion devices is designed to provide high performance through a flexible four-level hierarchy of routing resources: ultra-fast local resources; efficient long-line resources; high-speed very-long-line resources; and the high-performance VersaNet networks.

The ultra-fast local resources are dedicated lines that allow the output of each VersaTile to connect directly to every input of the eight surrounding VersaTiles (Figure 2-8). The exception to this is that the SET/CLR input of a VersaTile configured as a D-flip-flop is driven only by the VersaNet global network.

The efficient long-line resources provide routing for longer distances and higher-fanout connections. These resources vary in length (spanning one, two, or four VersaTiles), run both vertically and horizontally, and cover the entire Fusion device (Figure 2-9 on page 2-9). Each VersaTile can drive signals onto the efficient long-line resources, which can access every input of every VersaTile. Active buffers are inserted automatically by routing software to limit loading effects.

The high-speed very-long-line resources, which span the entire device with minimal delay, are used to route very long or high-fanout nets: length ± 12 VersaTiles in the vertical direction and length ± 16 in the horizontal direction from a given core VersaTile (Figure 2-10 on page 2-10). Very long lines in Fusion devices, like those in ProASIC3 devices, have been enhanced. This provides a significant performance boost for long-reach signals.

The high-performance VersaNet global networks are low-skew, high-fanout nets that are accessible from external pins or from internal logic (Figure 2-11 on page 2-11). These nets are typically used to distribute clocks, reset signals, and other high-fanout nets requiring minimum skew. The VersaNet networks are implemented as clock trees, and signals can be introduced at any junction. These can be employed hierarchically, with signals accessing every input on all VersaTiles.









Notes:

- 1. Visit the Microsemi SoC Products Group website for application notes concerning dynamic PLL reconfiguration. Refer to the "PLL Macro" section on page 2-27 for signal descriptions.
- 2. Many specific INBUF macros support the wide variety of single-ended and differential I/O standards for the Fusion family.
- 3. Refer to the IGLOO, ProASIC3, SmartFusion and Fusion Macro Library Guide for more information.

Figure 2-19 • Fusion CCC Options: Global Buffers with the PLL Macro

Table 2-11 • Available Selections of I/O Standards within CLKBUF and CLKBUF_LVDS/LVPECL Macros

CLKBUF Macros
CLKBUF_LVCMOS5
CLKBUF_LVCMOS33 ¹
CLKBUF_LVCMOS18
CLKBUF_LVCMOS15
CLKBUF_PCI
CLKBUF_LVDS ²
CLKBUF_LVPECL

Notes:

1. This is the default macro. For more details, refer to the IGLOO, ProASIC3, SmartFusion and Fusion Macro Library Guide.

2. The B-LVDS and M-LVDS standards are supported with CLKBUF_LVDS.





Figure 2-60 • FIFO EMPTY Flag and AEMPTY Flag Assertion



Device Architecture

ADC Input Multiplexer

At the input to the Fusion ADC is a 32:1 multiplexer. Of the 32 input channels, up to 30 are user definable. Two of these channels are hardwired internally. Channel 31 connects to an internal temperature diode so the temperature of the Fusion device itself can be monitored. Channel 0 is wired to the FPGA's 1.5 V VCC supply, enabling the Fusion device to monitor its own power supply. Doing this internally makes it unnecessary to use an analog I/O to support these functions. The balance of the MUX inputs are connected to Analog Quads (see the "Analog Quad" section on page 2-80). Table 2-40 defines which Analog Quad inputs are associated with which specific analog MUX channels. The number of Analog Quads present is device-dependent; refer to the family list in the "Fusion Family" table on page I of this datasheet for the number of quads per device. Regardless of the number of quads populated in a device, the internal connections to both VCC and the internal temperature diode remain on Channels 0 and 31, respectively. To sample the internal temperature monitor, it must be strobed (similar to the AT pads). The TMSTBINT pin on the Analog Block macro is the control for strobing the internal temperature measurement diode.

To determine which channel is selected for conversion, there is a five-pin interface on the Analog Block, CHNUMBER[4:0], defined in Table 2-39.

Channel Number	CHNUMBER[4:0]
0	00000
1	00001
2	00010
3	00011
•	•
30	11110
31	11111

Table 2-39 • Channel Selection

Table 2-40 shows the correlation between the analog MUX input channels and the analog input pins.

Table 2-40 • Analog MUX Channels

Analog MUX Channel	Signal	Analog Quad Number
0	Vcc_analog	
1	AV0	
2	AC0	Analog Quad 0
3	AT0	
4	AV1	
5	AC1	Analog Quad 1
6	AT1	
7	AV2	
8	AC2	Analog Quad 2
9	AT2	
10	AV3	
11	AC3	Analog Quad 3
12	AT3	
13	AV4	
14	AC4	Analog Quad 4
15	AT4	7

Table 2-49 • Analog Channel Specifications (continued)Commercial Temperature Range Conditions, TJ = 85°C (unless noted otherwise),Typical: VCC33A = 3.3 V, VCC = 1.5 V

Parameter	Description	Condition	Min.	Тур.	Max.	Units						
Temperature Monitor Using Analog Pad AT												
External	Resolution	8-bit ADC			4	°C						
Temperature		10-bit ADC			1	°C						
(external diode		12-bit ADC		0.25								
2N3904, T _J = 25°C) ⁴	Systematic Offset ⁵	AFS090, AFS250, AFS600, AFS1500, uncalibrated ⁷		5								
		AFS090, AFS250, AFS600, AFS1500, calibrated ⁷		±5								
	Accuracy			±3	±5	°C						
	External Sensor Source	High level, TMSTBx = 0		10		μA						
	Current	Low level, TMSTBx = 1		100		μA						
	Max Capacitance on AT pad				1.3	nF						
Internal	Resolution	8-bit ADC	4			°C						
Temperature		10-bit ADC	1			°C						
Mornton		12-bit ADC	0.25			°C						
	Systematic Offset ⁵	AFS090 ⁷			5	°C						
		AFS250, AFS600, AFS1500 ⁷			11	°C						
	Accuracy			±3	±5	°C						
t _{TMSHI}	Strobe High time		10		105	μs						
t _{TMSLO}	Strobe Low time		5			μs						
t _{TMSSET}	Settling time		5			μs						

Notes:

1. VRSM is the maximum voltage drop across the current sense resistor.

2. Analog inputs used as digital inputs can tolerate the same voltage limits as the corresponding analog pad. There is no reliability concern on digital inputs as long as VIND does not exceed these limits.

3. VIND is limited to VCC33A + 0.2 to allow reaching 10 MHz input frequency.

- 4. An averaging of 1,024 samples (LPF setting in Analog System Builder) is required and the maximum capacitance allowed across the AT pins is 500 pF.
- 5. The temperature offset is a fixed positive value.
- 6. The high current mode has a maximum power limit of 20 mW. Appropriate current limit resistors must be used, based on voltage on the pad.
- 7. When using SmartGen Analog System Builder, CalibIP is required to obtain specified offset. For further details on CalibIP, refer to the "Temperature, Voltage, and Current Calibration in Fusion FPGAs" chapter of the Fusion FPGA Fabric User Guide.

	Calib	orated Typica	Direct ADC ^{2,3} (%FSR)					
Input Voltage (V)	16 V (AT)	16 V (12 V) (AV/AC)	8 V (AV/AC)	4 V (AT)	4 V (AV/AC)	2 V (AV/AC)	1 V (AV/AC)	VAREF = 2.56 V
15	1							
14	1							
12	1	1						
5	2	2	1					
3.3	2	2	1	1	1			
2.5	3	2	1	1	1			1
1.8	4	4	1	1	1	1		1
1.5	5	5	2	2	2	1		1
1.2	7	6	2	2	2	1		1
0.9	9	9	4	3	3	1	1	1

Table 2-53 • Analog Channel Accuracy: Monitoring Standard Positive Voltages Typical Conditions, T_A = 25°C

Notes:

1. Requires enabling Analog Calibration using SmartGen Analog System Builder. For further details, refer to the "Temperature, Voltage, and Current Calibration in Fusion FPGAs" chapter of the Fusion FPGA Fabric User Guide.

2. Direct ADC mode using an external VAREF of 2.56V±4.6mV, without Analog Calibration macro.

3. For input greater than 2.56 V, the ADC output will saturate. A higher VAREF or prescaler usage is recommended.

Examples

Calculating Accuracy for an Uncalibrated Analog Channel

Formula

For a given prescaler range, EQ 30 gives the output voltage.

Output Voltage = (Channel Output Offset in V) + (Input Voltage x Channel Gain)

EQ 30

where

Channel Output offset in V = Channel Input offset in LSBs x Equivalent voltage per LSB Channel Gain Factor = 1 + (% Channel Gain / 100)

Example

Input Voltage = 5 V Chosen Prescaler range = 8 V range Refer to Table 2-51 on page 2-122.

Max. Output Voltage = (Max Positive input offset) + (Input Voltage x Max Positive Channel Gain)

Max. Positive input offset = (21 LSB) x (8 mV per LSB in 10-bit mode) Max. Positive input offset = 166 mV Max. Positive Gain Error = +3% Max. Positive Channel Gain = 1 + (+3% / 100) Max. Positive Channel Gain = 1.03 Max. Output Voltage = (166 mV) + (5 V x 1.03) Max. Output Voltage = **5.316 V**

Timing Characteristics

Table 2-55 • Analog Configuration Multiplexer (ACM) TimingCommercial Temperature Range Conditions: TJ = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	-2	-1	Std.	Units
t _{CLKQACM}	Clock-to-Q of the ACM	19.73	22.48	26.42	ns
t _{SUDACM}	Data Setup time for the ACM	4.39	5.00	5.88	ns
t _{HDACM}	Data Hold time for the ACM	0.00	0.00	0.00	ns
t _{SUAACM}	Address Setup time for the ACM	4.73	5.38	6.33	ns
t _{HAACM}	Address Hold time for the ACM	0.00	0.00	0.00	ns
t _{SUEACM}	Enable Setup time for the ACM	3.93	4.48	5.27	ns
t _{HEACM}	Enable Hold time for the ACM	0.00	0.00	0.00	ns
t _{MPWARACM}	Asynchronous Reset Minimum Pulse Width for the ACM	10.00	10.00	10.00	ns
t _{REMARACM}	Asynchronous Reset Removal time for the ACM	12.98	14.79	17.38	ns
t _{RECARACM}	Asynchronous Reset Recovery time for the ACM	12.98	14.79	17.38	ns
t _{MPWCLKACM}	Clock Minimum Pulse Width for the ACM	45.00	45.00	45.00	ns
t _{FMAXCLKACM}	lock Maximum Frequency for the ACM	10.00	10.00	10.00	MHz



Device Architecture

Analog Quad ACM Description

Table 2-56 maps out the ACM space associated with configuration of the Analog Quads within the Analog Block. Table 2-56 shows the byte assignment within each quad and the function of each bit within each byte. Subsequent tables will explain each bit setting and how it corresponds to a particular configuration. After 3.3 V and 1.5 V are applied to Fusion, Analog Quad configuration registers are loaded with default settings until the initialization and configuration state machine changes them to user-defined settings.

Table	2-56 •	Analog	Quad	Bvte /	Assianme	nt
1 4010	200	Analog	auuu .		Rooiginno	

Byte	Bit	Signal (Bx)	Function	Default Setting	
Byte 0	0	B0[0]	Scaling factor control – prescaler	Highest voltage range	
(AV)	1	B0[1]			
	2	B0[2]	-		
	3	B0[3]	Analog MUX select	Prescaler	
	4	B0[4]	Current monitor switch	Off	
	5	B0[5]	Direct analog input switch	Off	
	6	B0[6]	Selects V-pad polarity	Positive	
	7	B0[7]	Prescaler op amp mode	Power-down	
Byte 1	0	B1[0]	Scaling factor control – prescaler	Highest voltage range	
(AC)	1	B1[1]			
	2	B1[2]			
	3	B1[3]	Analog MUX select	Prescaler	
	4	B1[4]			
	5	B1[5]	Direct analog input switch	Off	
	6	B1[6]	Selects C-pad polarity	Positive	
	7	B1[7]	Prescaler op amp mode	Power-down	
Byte 2	0	B2[0]	Internal chip temperature monitor *	Off	
(AG)	1	B2[1]	Spare	-	
	2	B2[2]	Current drive control	Lowest current	
	3	B2[3]			
	4	B2[4]	Spare	-	
	5	B2[5]	Spare	-	
	6	B2[6]	Selects G-pad polarity	Positive	
	7	B2[7]	Selects low/high drive	Low drive	
Byte 3	0	B3[0]	Scaling factor control – prescaler	Highest voltage range	
(AT)	1	B3[1]	-		
	2	B3[2]	-		
	3	B3[3]	Analog MUX select	Prescaler	
	4	B3[4]			
	5	B3[5]	Direct analog input switch	Off	
	6	B3[6]	_	-	
	7	B3[7]	Prescaler op amp mode	Power-down	

Note: *For the internal temperature monitor to function, Bit 0 of Byte 2 for all 10 Quads must be set.



Device Architecture

Table 2-105 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew

Commercial Temperature Range Conditions: $T_J = 70^{\circ}$ C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V Applicable to Pro I/Os

Drive	Speed						^τ ΕΟU							11
Strength	Grade	TDOUT	τ _{DP}	τ _{DIN}	τ _{ΡΥ}	τ _{PYS}	Т	۲ZL	τzΗ	ιLZ	τ _{HZ}	τ _{ZLS}	τ _{zhs}	Units
4 mA	Std.	0.66	7.88	0.04	1.20	1.57	0.43	8.03	6.70	2.69	2.59	10.26	8.94	ns
	-1	0.56	6.71	0.04	1.02	1.33	0.36	6.83	5.70	2.29	2.20	8.73	7.60	ns
	-2	0.49	5.89	0.03	0.90	1.17	0.32	6.00	5.01	2.01	1.93	7.67	6.67	ns
8 mA	Std.	0.66	5.08	0.04	1.20	1.57	0.43	5.17	4.14	3.05	3.21	7.41	6.38	ns
	-1	0.56	4.32	0.04	1.02	1.33	0.36	4.40	3.52	2.59	2.73	6.30	5.43	ns
	-2	0.49	3.79	0.03	0.90	1.17	0.32	3.86	3.09	2.28	2.40	5.53	4.76	ns
12 mA	Std.	0.66	3.67	0.04	1.20	1.57	0.43	3.74	2.87	3.28	3.61	5.97	5.11	ns
	-1	0.56	3.12	0.04	1.02	1.33	0.36	3.18	2.44	2.79	3.07	5.08	4.34	ns
	-2	0.49	2.74	0.03	0.90	1.17	0.32	2.79	2.14	2.45	2.70	4.46	3.81	ns
16 mA	Std.	0.66	3.46	0.04	1.20	1.57	0.43	3.53	2.61	3.33	3.72	5.76	4.84	ns
	-1	0.56	2.95	0.04	1.02	1.33	0.36	3.00	2.22	2.83	3.17	4.90	4.12	ns
	-2	0.49	2.59	0.03	0.90	1.17	0.32	2.63	1.95	2.49	2.78	4.30	3.62	ns
24 mA	Std.	0.66	3.21	0.04	1.20	1.57	0.43	3.27	2.16	3.39	4.13	5.50	4.39	ns
	-1	0.56	2.73	0.04	1.02	1.33	0.36	2.78	1.83	2.88	3.51	4.68	3.74	ns
	-2	0.49	2.39	0.03	0.90	1.17	0.32	2.44	1.61	2.53	3.08	4.11	3.28	ns

Table 2-114 • 2.5 V LVCMOS Low Slew

Commercial Temperature Range Conditions: $T_J = 70^{\circ}$ C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V Applicable to Advanced I/Os

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{zH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{zHS}	Units
4 mA	Std.	0.66	11.40	0.04	1.31	0.43	11.22	11.40	2.68	2.20	13.45	13.63	ns
	-1	0.56	9.69	0.04	1.11	0.36	9.54	9.69	2.28	1.88	11.44	11.60	ns
	-2	0.49	8.51	0.03	0.98	0.32	8.38	8.51	2.00	1.65	10.05	10.18	ns
8 mA	Std.	0.66	7.96	0.04	1.31	0.43	8.11	7.81	3.05	2.89	10.34	10.05	ns
	-1	0.56	6.77	0.04	1.11	0.36	6.90	6.65	2.59	2.46	8.80	8.55	ns
	-2	0.49	5.94	0.03	0.98	0.32	6.05	5.84	2.28	2.16	7.72	7.50	ns
12 mA	Std.	0.66	6.18	0.04	1.31	0.43	6.29	5.92	3.30	3.32	8.53	8.15	ns
	-1	0.56	5.26	0.04	1.11	0.36	5.35	5.03	2.81	2.83	7.26	6.94	ns
	-2	0.49	4.61	0.03	0.98	0.32	4.70	4.42	2.47	2.48	6.37	6.09	ns
16 mA	Std.	0.66	6.18	0.04	1.31	0.43	6.29	5.92	3.30	3.32	8.53	8.15	ns
	-1	0.56	5.26	0.04	1.11	0.36	5.35	5.03	2.81	2.83	7.26	6.94	ns
	-2	0.49	4.61	0.03	0.98	0.32	4.70	4.42	2.47	2.48	6.37	6.09	ns
24 mA	Std.	0.66	6.18	0.04	1.31	0.43	6.29	5.92	3.30	3.32	8.53	8.15	ns
	-1	0.56	5.26	0.04	1.11	0.36	5.35	5.03	2.81	2.83	7.26	6.94	ns
	-2	0.49	4.61	0.03	0.98	0.32	4.70	4.42	2.47	2.48	6.37	6.09	ns

Table 2-125 • 1.8 V LVCMOS High Slew
Commercial Temperature Range Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCI = 1.7 V
Applicable to Standard I/Os

Drive	Speed										
Strength	Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	Units
2 mA	Std.	0.66	11.21	0.04	1.20	0.43	8.53	11.21	1.99	1.21	ns
	-1	0.56	9.54	0.04	1.02	0.36	7.26	9.54	1.69	1.03	ns
	-2	0.49	8.37	0.03	0.90	0.32	6.37	8.37	1.49	0.90	ns
4 mA	Std.	0.66	6.34	0.04	1.20	0.43	5.38	6.34	2.41	2.48	ns
	-1	0.56	5.40	0.04	1.02	0.36	4.58	5.40	2.05	2.11	ns
	-2	0.49	4.74	0.03	0.90	0.32	4.02	4.74	1.80	1.85	ns

2.5 V GTL+

Gunning Transceiver Logic Plus is a high-speed bus standard (JESD8-3). It provides a differential amplifier input buffer and an open-drain output buffer. The VCCI pin should be connected to 2.5 V.

Table 2-147 • Minimum and Maximum DC Input and Output Levels

2.5 V GTL+		VIL	VIH		VOL	VOH	IOL	ЮН	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
33 mA	-0.3	VREF – 0.1	VREF + 0.1	3.6	0.6	_	33	33	124	169	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where -0.3 V < VIN < VIL.

2. IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.

3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.

4. Currents are measured at 85°C junction temperature.



Figure 2-127 • AC Loading

Table 2-148 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C _{LOAD} (pF)
VREF – 0.1	VREF + 0.1	1.0	1.0	1.5	10

Note: *Measuring point = Vtrip. See Table 2-90 on page 2-166 for a complete table of trip points.

Timing Characteristics

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Table 2-149 • 2.5 V GTL+
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Commercial Temperature Range Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V, VREF = 1.0 V

Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{zHS}	Units
Std.	0.66	2.21	0.04	1.51	0.43	2.25	2.10			4.48	4.34	ns
-1	0.56	1.88	0.04	1.29	0.36	1.91	1.79			3.81	3.69	ns
-2	0.49	1.65	0.03	1.13	0.32	1.68	1.57			3.35	4.34	ns



Table 2-174 • Parameter Definitions and Measuring Nodes

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t _{OCLKQ}	Clock-to-Q of the Output Data Register	H, DOUT
tosud	Data Setup Time for the Output Data Register	F, H
t _{OHD}	Data Hold Time for the Output Data Register	F, H
t _{OSUE}	Enable Setup Time for the Output Data Register	G, H
t _{OHE}	Enable Hold Time for the Output Data Register	G, H
t _{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	L,DOUT
t _{OREMPRE}	Asynchronous Preset Removal Time for the Output Data Register	L, H
t _{ORECPRE}	Asynchronous Preset Recovery Time for the Output Data Register	L, H
t _{OECLKQ}	Clock-to-Q of the Output Enable Register	H, EOUT
t _{OESUD}	Data Setup Time for the Output Enable Register	J, H
t _{OEHD}	Data Hold Time for the Output Enable Register	J, H
t _{OESUE}	Enable Setup Time for the Output Enable Register	K, H
t _{OEHE}	Enable Hold Time for the Output Enable Register	K, H
t _{OEPRE2Q}	Asynchronous Preset-to-Q of the Output Enable Register	I, EOUT
t _{OEREMPRE}	Asynchronous Preset Removal Time for the Output Enable Register	I, H
t _{OERECPRE}	Asynchronous Preset Recovery Time for the Output Enable Register	I, H
t _{ICLKQ}	Clock-to-Q of the Input Data Register	A, E
t _{ISUD}	Data Setup Time for the Input Data Register	C, A
t _{IHD}	Data Hold Time for the Input Data Register	C, A
t _{ISUE}	Enable Setup Time for the Input Data Register	B, A
t _{IHE}	Enable Hold Time for the Input Data Register	B, A
t _{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	D, E
t _{IREMPRE}	Asynchronous Preset Removal Time for the Input Data Register	D, A
t _{IRECPRE}	Asynchronous Preset Recovery Time for the Input Data Register	D, A

Note: *See Figure 2-137 on page 2-212 for more information.



DDR Module Specifications

Input DDR Module



Figure 2-142 • Input DDR Timing Model

Table 2-179 • Parameter Definitions

Parameter Name	Parameter Definition	Measuring Nodes (from, to)
t _{DDRICLKQ1}	Clock-to-Out Out_QR	B, D
t _{DDRICLKQ2}	Clock-to-Out Out_QF	B, E
t _{DDRISUD}	Data Setup Time of DDR Input	А, В
t _{DDRIHD}	Data Hold Time of DDR Input	А, В
t _{DDRICLR2Q1}	Clear-to-Out Out_QR	C, D
t _{DDRICLR2Q2}	Clear-to-Out Out_QF	C, E
t _{DDRIREMCLR}	Clear Removal	С, В
t _{DDRIRECCLR}	Clear Recovery	С, В



Symbol	Parameter ²		Commercial	Industrial	Units
Τ _J	Junction temperature		0 to +85	-40 to +100	°C
VCC	1.5 V DC core supply voltage	1.425 to 1.575	1.425 to 1.575	V	
VJTAG	JTAG DC voltage		1.4 to 3.6	1.4 to 3.6	V
VPUMP	Programming voltage	Programming mode ³	3.15 to 3.45	3.15 to 3.45	V
		Operation ⁴	0 to 3.6	0 to 3.6	V
VCCPLL	Analog power supply (PLL)		1.425 to 1.575	1.425 to 1.575	V
VCCI	1.5 V DC supply voltage		1.425 to 1.575	1.425 to 1.575	V
	1.8 V DC supply voltage		1.7 to 1.9	1.7 to 1.9	V
	2.5 V DC supply voltage		2.3 to 2.7	2.3 to 2.7	V
	3.3 V DC supply voltage		3.0 to 3.6	3.0 to 3.6	V
	LVDS differential I/O	2.375 to 2.625	2.375 to 2.625	V	
	LVPECL differential I/O		3.0 to 3.6	3.0 to 3.6	V
VCC33A	+3.3 V power supply		2.97 to 3.63	2.97 to 3.63	V
VCC33PMP	+3.3 V power supply	2.97 to 3.63	2.97 to 3.63	V	
VAREF	Voltage reference for ADC	2.527 to 2.593	2.527 to 2.593	V	
VCC15A ⁵	Digital power supply for the analog	1.425 to 1.575	1.425 to 1.575	V	
VCCNVM	Embedded flash power supply	1.425 to 1.575	1.425 to 1.575	V	
VCCOSC	Oscillator power supply		2.97 to 3.63	2.97 to 3.63	V
AV, AC ⁶	Unpowered, ADC reset asserted or	-10.5 to 12.0	-10.5 to 11.6	V	
	Analog input (+16 V to +2 V presca	ller range)	-0.3 to 12.0	–0.3 to 11.6	V
	Analog input (+1 V to + 0.125 V pre	escaler range)	-0.3 to 3.6	-0.3 to 3.6	V
	Analog input (–16 V to –2 V presca	ler range)	-10.5 to 0.3	-10.5 to 0.3	V
	Analog input (–1 V to –0.125 V pres	scaler range)	-3.6 to 0.3	-3.6 to 0.3	V
	Analog input (direct input to ADC)		-0.3 to 3.6	-0.3 to 3.6	V
	Digital input		-0.3 to 12.0	–0.3 to 11.6	V
AG ⁶	Unpowered, ADC reset asserted or	unconfigured	-10.5 to 12.0	-10.5 to 11.6	V
	Low Current Mode (1 µA, 3 µA, 10	μΑ, 30 μΑ)	-0.3 to 12.0	–0.3 to 11.6	V
	Low Current Mode (–1 µA, –3 µA, -	–10 μA, –30 μA)	-10.5 to 0.3	-10.5 to 0.3	V
	High Current Mode ⁷	-10.5 to 12.0	-10.5 to 11.6	V	
AT ⁶	Unpowered, ADC reset asserted or	-0.3 to 15.5	–0.3 to 14.5	V	
	Analog input (+16 V, +4 V prescale	r range)	–0.3 to 15.5	–0.3 to 14.5	V
	Analog input (direct input to ADC)		-0.3 to 3.6	-0.3 to 3.6	V
	Digital input		-0.3 to 15.5	-0.3 to 14.5	V

Table 3-2 • Recommended Operating Conditions¹

Notes:

1. The ranges given here are for power supplies only. The recommended input voltage ranges specific to each I/O standard are given in Table 2-85 on page 2-157.

- 2. All parameters representing voltages are measured with respect to GND unless otherwise specified.
- 3. The programming temperature range supported is $T_{ambient} = 0^{\circ}C$ to 85°C.
- 4. VPUMP can be left floating during normal operation (not programming mode).
- 5. Violating the V_{CC15A} recommended voltage supply during an embedded flash program cycle can corrupt the page being programmed.
- 6. The input voltage may overshoot by up to 500 mV above the Recommended Maximum (150 mV in Direct mode), provided the duration of the overshoot is less than 50% of the operating lifetime of the device.
- 7. The AG pad should also conform to the limits as specified in Table 2-48 on page 2-114.

Pads	Pad Configuration	Prescaler Range	Input Resistance to Ground	
AV, AC	Analog Input (direct input to ADC)	-	2 kΩ (typical)	
		-	> 10 MΩ	
	Analog Input (positive prescaler)	+16 V to +2 V	1 MΩ (typical)	
		+1 V to +0.125 V	> 10 MΩ	
	Analog Input (negative prescaler)	–16 V to –2 V	1 MΩ (typical)	
		–1 V to –0.125 V	> 10 MΩ	
	Digital input	+16 V to +2 V	1 MΩ (typical)	
	Current monitor	+16 V to +2 V	1 MΩ (typical)	
		–16 V to –2 V	1 MΩ (typical)	
AT	Analog Input (direct input to ADC)	-	1 MΩ (typical)	
	Analog Input (positive prescaler)	+16 V, +4 V	1 MΩ (typical)	
	Digital input	+16 V, +4 V	1 MΩ (typical)	
	Temperature monitor	+16 V, +4 V	> 10 MΩ	

Table 3-3 • Input Resistance of Analog Pads

Table 3-4 • Overshoot and Undershoot Limits ¹

vccı	Average VCCI–GND Overshoot or Undershoot Duration as a Percentage of Clock Cycle ²	Maximum Overshoot/ Undershoot ²
2.7 V or less	10%	1.4 V
	5%	1.49 V
3.0 V	10%	1.1 V
	5%	1.19 V
3.3 V	10%	0.79 V
	5%	0.88 V
3.6 V	10%	0.45 V
	5%	0.54 V

Notes:

1. Based on reliability requirements at a junction temperature of 85°C.

2. The duration is allowed at one cycle out of six clock cycle. If the overshoot/undershoot occurs at one out of two cycles, the maximum overshoot/undershoot has to be reduced by 0.15 V.



Table 3-12 • Summary of I/O Input Buffer Power (per pin)—Default I/O Software Settings (continued)

	VCCI (V)	Static Power PDC7 (mW) ¹	Dynamic Power PAC9 (µW/MHz) ²
Applicable to Advanced I/O Banks			
Single-Ended			
3.3 V LVTTL/LVCMOS	3.3	_	16.69
2.5 V LVCMOS	2.5	_	5.12
1.8 V LVCMOS	1.8	_	2.13
1.5 V LVCMOS (JESD8-11)	1.5	_	1.45
3.3 V PCI	3.3	_	18.11
3.3 V PCI-X	3.3	_	18.11
Differential			
LVDS	2.5	2.26	1.20
LVPECL	3.3	5.72	1.87
Applicable to Standard I/O Banks			
3.3 V LVTTL/LVCMOS	3.3	-	16.79
2.5 V LVCMOS	2.5	_	5.19
1.8 V LVCMOS	1.8	_	2.18
1.5 V LVCMOS (JESD8-11)	1.5	_	1.52

Notes:

1. PDC7 is the static power (where applicable) measured on VCCI.

2. PAC9 is the total dynamic power measured on VCC and VCCI.



Static Power Consumption of Various Internal Resources

Table 3-15 • Different Components Contributing to the Static Power Consumption in Fusion Devices

		Power		Device-Specific Static Contributions			ibutions	
Parameter	Definition	Supply		AFS1500	AFS600	AFS250	AFS090	Units
PDC1	Core static power contribution in operating mode	VCC	1.5 V	18	7.5	4.50	3.00	mW
PDC2	Device static power contribution in standby mode	VCC33A	3.3 V	0.66				mW
PDC3	Device static power contribution in sleep mode	VCC33A	3.3 V	3 V 0.03				mW
PDC4	NVM static power contribution	VCC	1.5 V		1.1	19		mW
PDC5	Analog Block static power contribution of ADC	VCC33A	3.3 V	3 V 8.25				mW
PDC6	Analog Block static power contribution per Quad	VCC33A	3.3 V 3.3					mW
PDC7	Static contribution per input pin – standard dependent contribution	VCCI	See Table 3-12 on page 3-18					
PDC8	Static contribution per input pin – standard dependent contribution	VCCI	See Table 3-13 on page 3-20			3-20		
PDC9	Static contribution for PLL	VCC	1.5 V 2.55				mW	

Power Calculation Methodology

This section describes a simplified method to estimate power consumption of an application. For more accurate and detailed power estimations, use the SmartPower tool in the Libero SoC software.

The power calculation methodology described below uses the following variables:

- The number of PLLs as well as the number and the frequency of each output clock generated
- · The number of combinatorial and sequential cells used in the design
- The internal clock frequencies
- · The number and the standard of I/O pins used in the design
- The number of RAM blocks used in the design
- The number of NVM blocks used in the design
- The number of Analog Quads used in the design
- Toggle rates of I/O pins as well as VersaTiles—guidelines are provided in Table 3-16 on page 3-27.
- Enable rates of output buffers—guidelines are provided for typical applications in Table 3-17 on page 3-27.
- Read rate and write rate to the RAM—guidelines are provided for typical applications in Table 3-17 on page 3-27.
- Read rate to the NVM blocks

The calculation should be repeated for each clock domain defined in the design.

FG256								
Pin Number	AFS090 Function	AFS250 Function	AFS600 Function	AFS1500 Function				
R5	AV0	AV0	AV2	AV2				
R6	AT0	AT0	AT2	AT2				
R7	AV1	AV1	AV3	AV3				
R8	AT3	AT3	AT5	AT5				
R9	AV4	AV4	AV6	AV6				
R10	NC	AT5	AT7	AT7				
R11	NC	AV5	AV7	AV7				
R12	NC	NC	AT9	AT9				
R13	NC	NC	AG9	AG9				
R14	NC	NC	AC9	AC9				
R15	PUB	PUB	PUB	PUB				
R16	VCCIB1	VCCIB1	VCCIB2	VCCIB2				
T1	GND	GND	GND	GND				
T2	NCAP	NCAP	NCAP	NCAP				
Т3	VCC33N	VCC33N	VCC33N	VCC33N				
T4	NC	NC	ATRTN0	ATRTN0				
T5	AT1	AT1	AT3	AT3				
Т6	ATRTN0	ATRTN0	ATRTN1	ATRTN1				
Τ7	AT2	AT2	AT4	AT4				
Т8	ATRTN1	ATRTN1	ATRTN2	ATRTN2				
Т9	AT4	AT4	AT6	AT6				
T10	ATRTN2	ATRTN2	ATRTN3	ATRTN3				
T11	NC	NC	AT8	AT8				
T12	NC	NC	ATRTN4	ATRTN4				
T13	GNDA	GNDA	GNDA	GNDA				
T14	VCC33A	VCC33A	VCC33A	VCC33A				
T15	VAREF	VAREF	VAREF	VAREF				
T16	GND	GND	GND	GND				



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